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LED470-66-16100

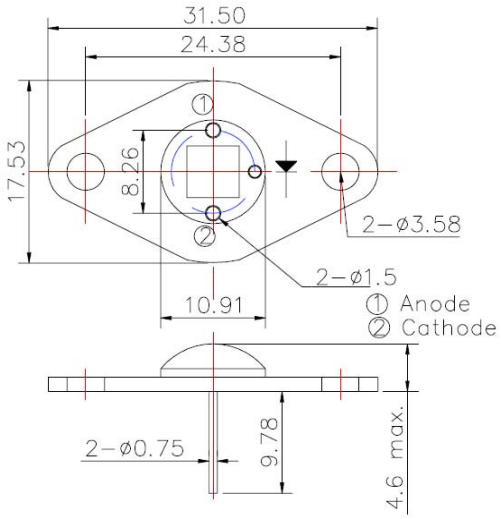
TECHNICAL DATA

High Power LED Array, 4 x 4 matrix InGaN

LED470-66-16100 is composed by 16pcs. of 1 x 1 mm² high current drive InGaN blue color diode chips, mounted on a metal stem TO-66 and covered with epoxy resin.
It is designed for wide viewing and extremely high output power illuminator.

Specifications

- Structure: InGaN, 16 power LED chips, 4 x 4 array
- Peak Wavelength: typ. 465 nm
- Optical Output Power: typ. 420 mW
- Package: TO-66 stem,
  clear silicone and epoxy resin



(Unit: mm)

Absolute Maximum Ratings (T_C=25°C)

Item	Symbol	Value	Unit
Power Dissipation	P_D	8.5	W
Forward Current	I_F	1.6	A
Pulse Forward Current *1	I_{FP}	2.0	A
Reverse Voltage	V_R	30	V
Operating Temperature	T_{opr}	-30 … +80	°C
Storage Temperature	T_{stg}	-30 … +100	°C
Soldering Temperature *2	T_{sol}	265	°C

*1 duty cycle = 1%, pulse width = 1µs
*2 must be completed within 3 seconds

Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 1.2 A	-	14.0	-	V
Brightness	I_V	I_F = 1.2 A	-	-	-	cd
Total Radiated Power	P_O	I_F = 1.2 A	-	420	-	mW
Reverse Voltage	V_R	I_R = 10 µA	20	-	-	V
Peak Wavelength	λ_P	I_F = 1.2 A	-	465	-	nm
Half Width	$\Delta\lambda$	I_F = 1.2 A	-	20	-	nm
Viewing Half Angle	$\Theta_{1/2}$	I_F = 1.2 A	-	±55	-	deg.

LED is required to keep less than 60°C

Notes

- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.